

N-Channel 80 V (D-S) MOSFET

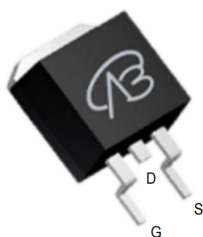
PRODUCT SUMMARY

V_{DS}	80	V
$R_{DS(on)} V_{GS} = 10\text{ V}$	6	$m\Omega$
$R_{DS(on)} V_{GS} = 4.5\text{ V}$	10	$m\Omega$
I_D	120	A
Configuration	Single	

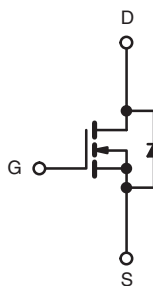
FEATURES

- Thunder power MOSFET
- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see


RoHS
 COMPLIANT

TO-263


Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 150\text{ }^\circ\text{C}$)	$T_C = 25\text{ }^\circ\text{C}$	I_D	120	A
	$T_C = 125\text{ }^\circ\text{C}$		65	
Pulsed Drain Current ($t = 100\text{ }\mu\text{s}$)		I_{DM}	225	
Avalanche Current	$L = 0.1\text{ mH}$	I_{AS}	90	
Single Avalanche Energy ^a		E_{AS}	405	mJ
Maximum Power Dissipation ^a	$T_C = 25\text{ }^\circ\text{C}$	P_D	370 ^b	W
	$T_C = 125\text{ }^\circ\text{C}$		120 ^b	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) ^c	R_{thJA}	40	$^\circ\text{C/W}$
Junction-to-Case (Drain)	R_{thJC}	0.75	

Notes

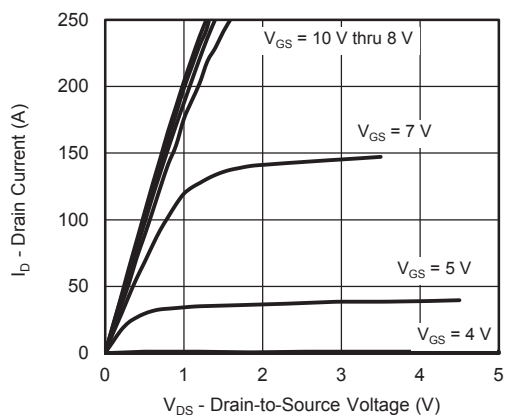
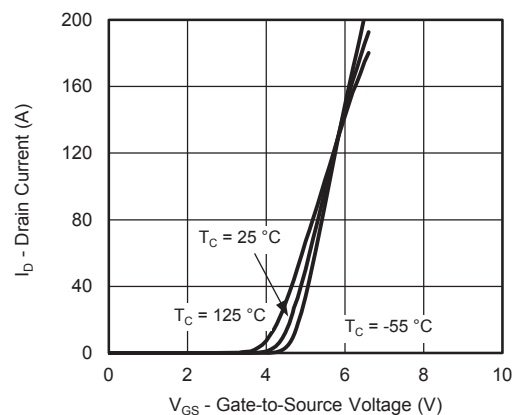
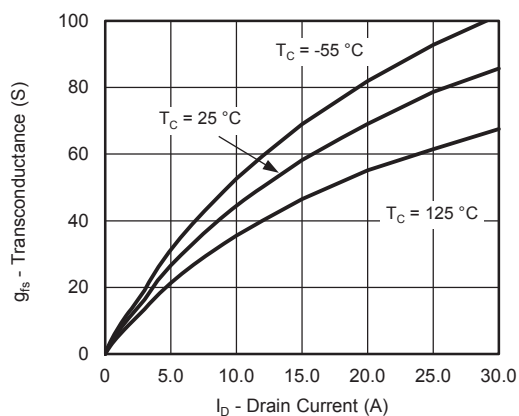
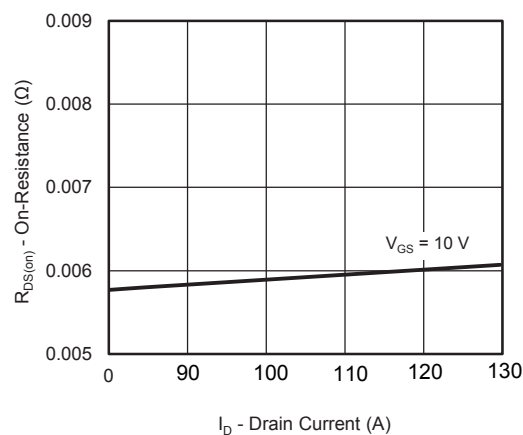
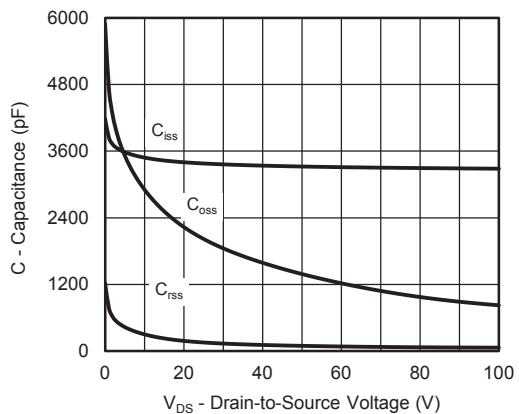
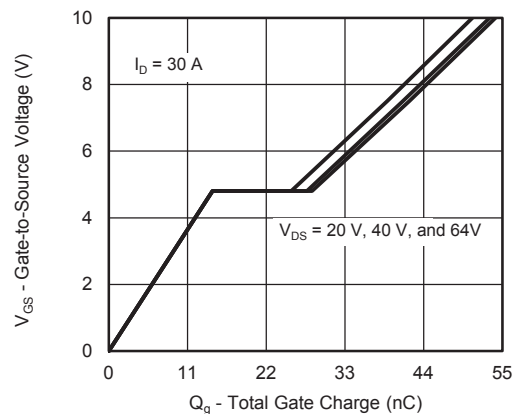
- Duty cycle $\leq 1\%$.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR4 material).

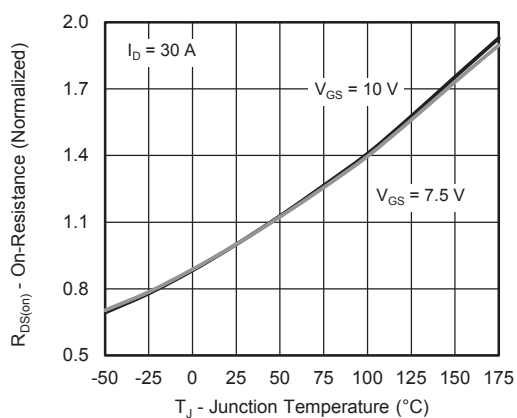
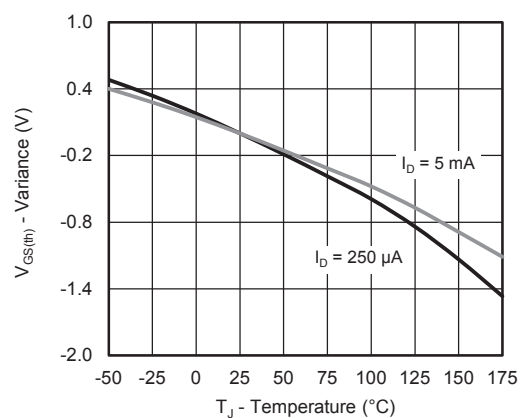
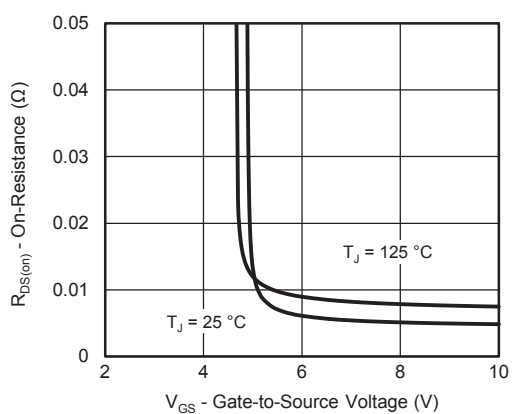
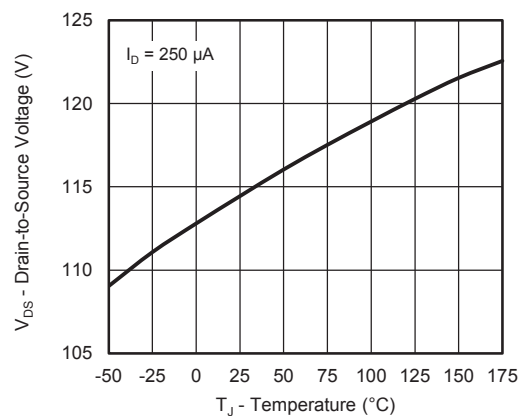
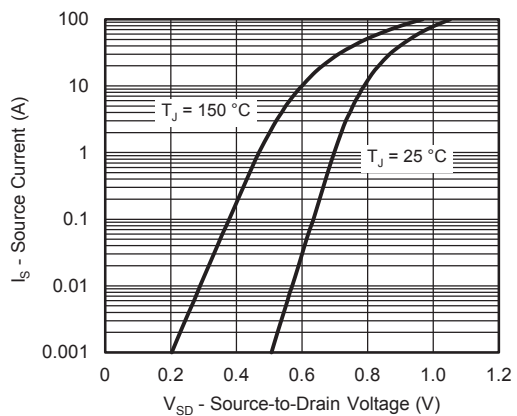
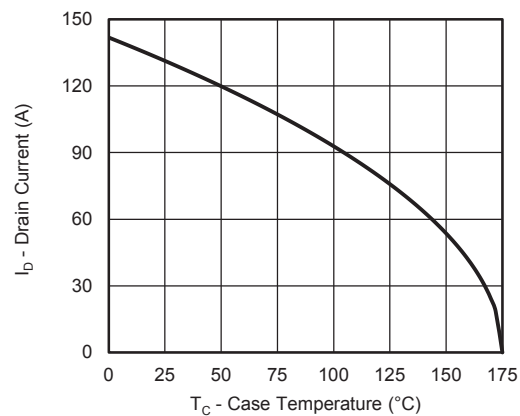
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	80	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.5	-	4.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 80 V, V _{GS} = 0 V, T _J = 125 °C	-	-	100	
		V _{DS} = 80 V, V _{GS} = 0 V, T _J = 175 °C	-	-	2	mA
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	90	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A	-	6	-	mΩ
		V _{GS} = 4.5V, I _D = 30 A	-	10	-	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 30 A	-	85	-	S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 40 V, f = 1 MHz	-	6400	-	pF
Output Capacitance	C _{oss}		-	1395	-	
Reverse Transfer Capacitance	C _{rss}		-	95	-	
Total Gate Charge ^c	Q _g	V _{DS} = 40 V, V _{GS} = 10 V, I _D = 30 A	-	53.5	81	nC
Gate-Source Charge ^c	Q _{gs}		-	14.5	-	
Gate-Drain Charge ^c	Q _{gd}		-	13.2	-	
Gate Resistance	R _g	f = 1 MHz	0.9	1.9	3.8	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 40 V, R _L = 1.67 Ω I _D ≅ 30 A, V _{GEN} = 10 V, R _g = 1 Ω	-	13	26	ns
Rise Time ^c	t _r		-	22	44	
Turn-Off Delay Time ^c	t _{d(off)}		-	27	54	
Fall Time ^c	t _f		-	9	18	
Drain-Source Body Diode Ratings and Characteristics ^b (T _C = 25 °C)						
Pulsed Current (t = 100 μs)	I _{SM}		-	-	240	A
Forward Voltage ^a	V _{SD}	I _F = 30 A, V _{GS} = 0 V	-	0.86	1.4	V
Reverse Recovery Time	t _{rr}	I _F = 30 A, di/dt = 100 A/μs	-	88	176	ns
Peak Reverse Recovery Charge	I _{RM(REC)}		-	5	10	A
Reverse Recovery Charge	Q _{rr}		-	0.22	0.44	μC

Notes

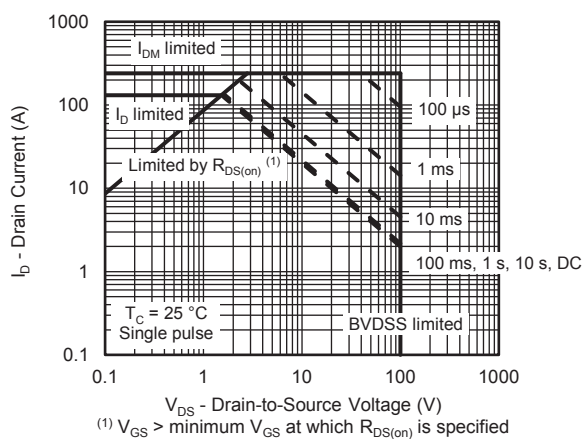
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

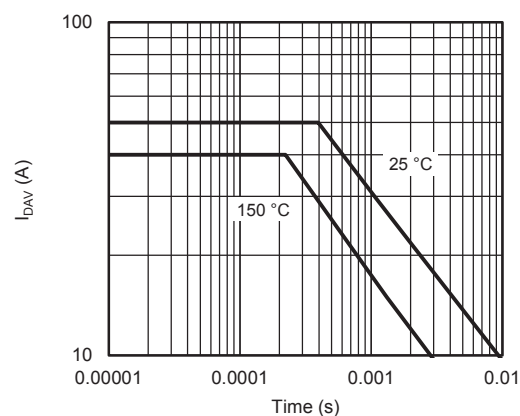
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

Threshold Voltage

On-Resistance vs. Gate-to-Source Voltage

Drain Source Breakdown vs. Junction Temperature

Source Drain Diode Forward Voltage

Current De-Rating

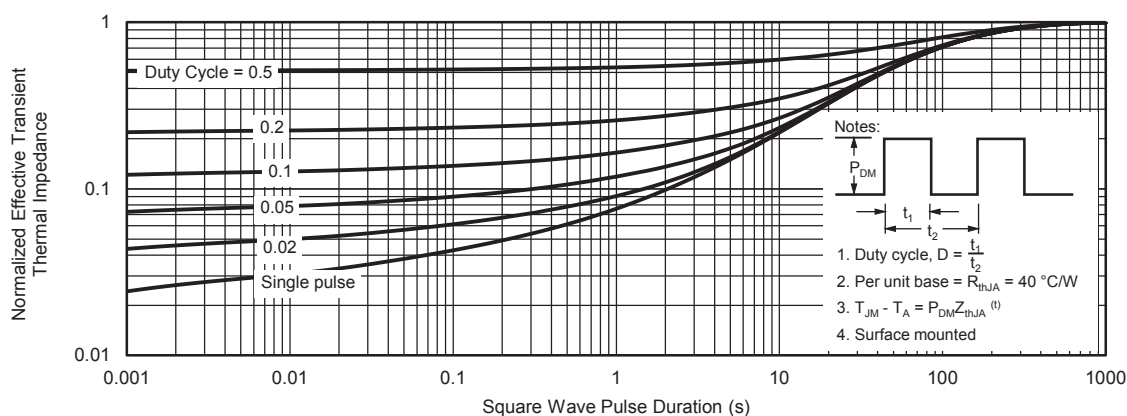
THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



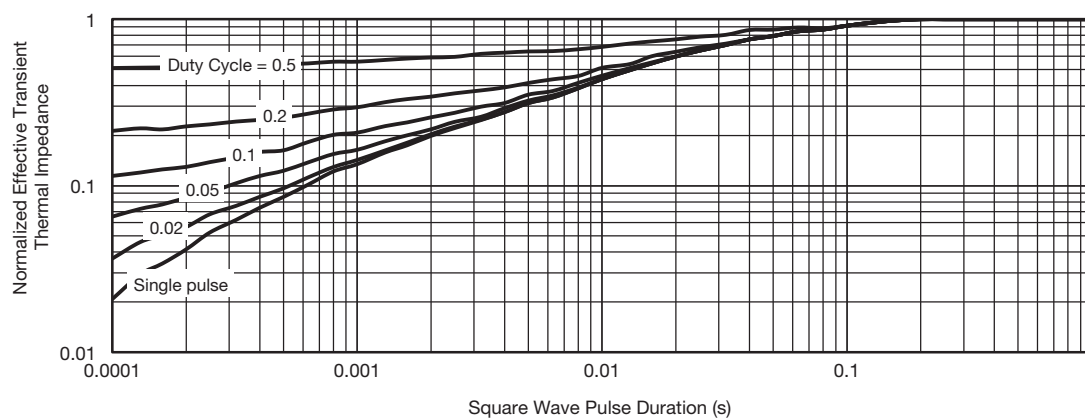
Safe Operating Area



I_{DAV} vs. Time



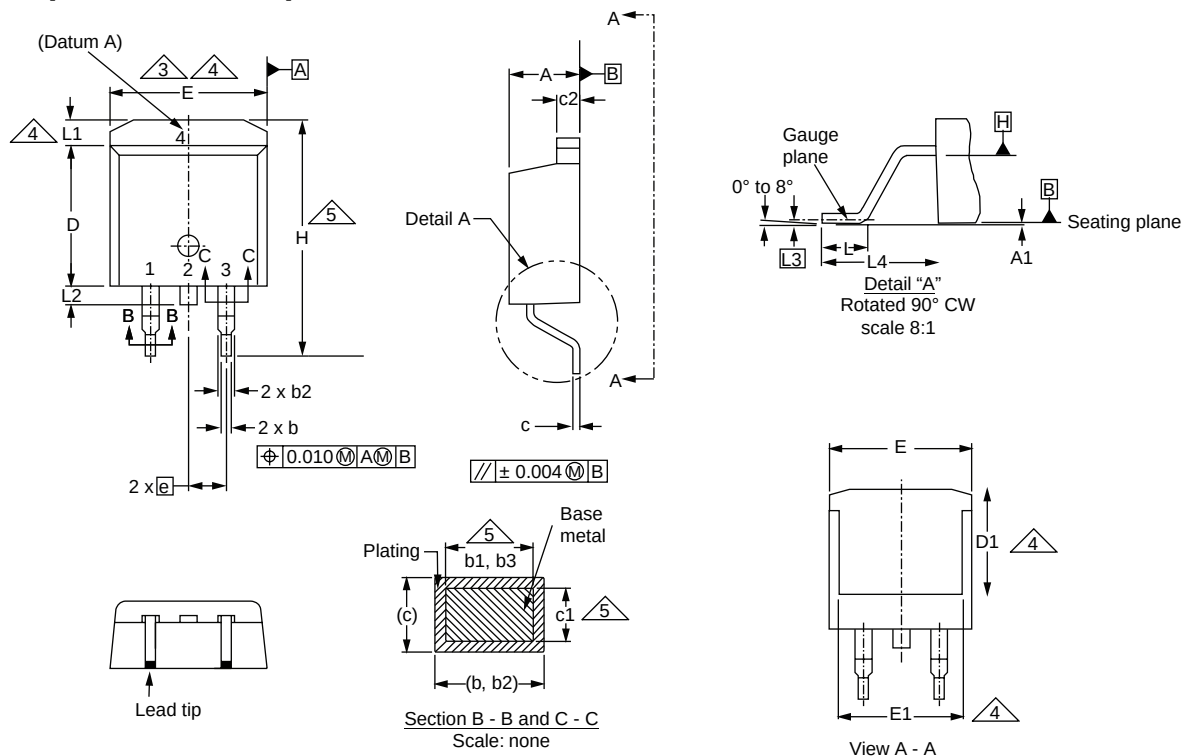
Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction to Case ($25\text{ }^{\circ}\text{C}$)are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-263AB (HIGH VOLTAGE)

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

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